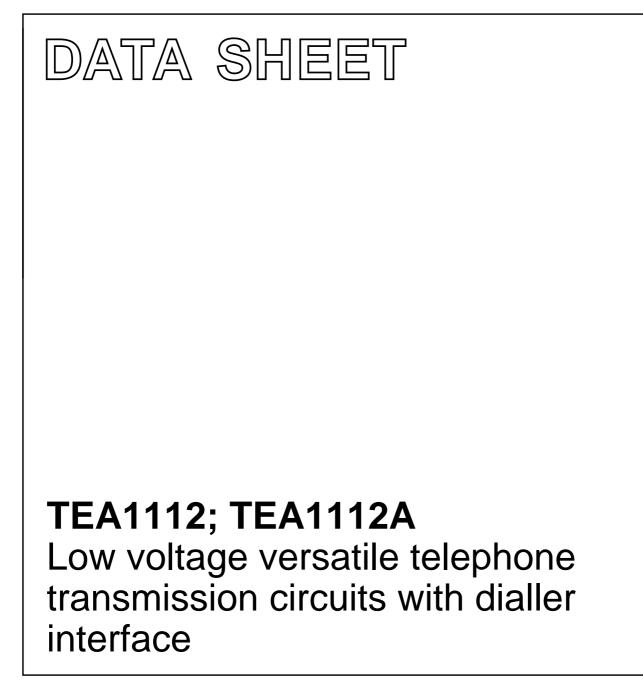
INTEGRATED CIRCUITS



Product specification Supersedes data of 1996 Feb 16 File under Integrated Circuits, IC03 1997 Mar 26



### TEA1112; TEA1112A

### FEATURES

- Low DC line voltage; operates down to 1.6 V (excluding polarity guard)
- Voltage regulator with adjustable DC voltage
- Provides a supply for external circuits
- Symmetrical high impedance inputs (64 kΩ) for dynamic, magnetic or piezo-electric microphones
- Asymmetrical high impedance input (32  $k\Omega)$  for electret microphones
- DTMF input with confidence tone
- Mute input for pulse or DTMF dialling (MUTE for TEA1112 and MUTE for TEA1112A)
- Receiving amplifier for dynamic, magnetic or piezo-electric earpieces
- AGC line loss compensation for microphone and earpiece amplifiers
- LED on-hook/off-hook status indication
- Microphone mute function (MMUTE for TEA1112 and MMUTE for TEA1112A).

### APPLICATION

• Line powered telephone sets, cordless telephones, fax machines and answering machines.

### **GENERAL DESCRIPTION**

The TEA1112; TEA1112A are bipolar integrated circuits that perform all speech and line interface functions required in fully electronic telephone sets. They perform electronic switching between speech and dialling. The ICs operate at a line voltage down to 1.6 V DC (with reduced performance) to facilitate the use of telephone sets connected in parallel.

A current (proportional to the line current and internally limited to a typical value of 19.5 mA) is available to drive an LED which indicates the on-hook/off-hook status.

The microphone amplifier can be disabled during speech condition by means of a microphone mute function.

All statements and values refer to all versions unless otherwise specified.

### QUICK REFERENCE DATA

 $I_{line}$  = 15 mA;  $V_{EE}$  = 0 V;  $R_{SLPE}$  = 20  $\Omega$ ; AGC pin connected to  $V_{EE}$ ;  $Z_{line}$  = 600  $\Omega$ ; f = 1 kHz;  $T_{amb}$  = 25 °C; unless otherwise specified.

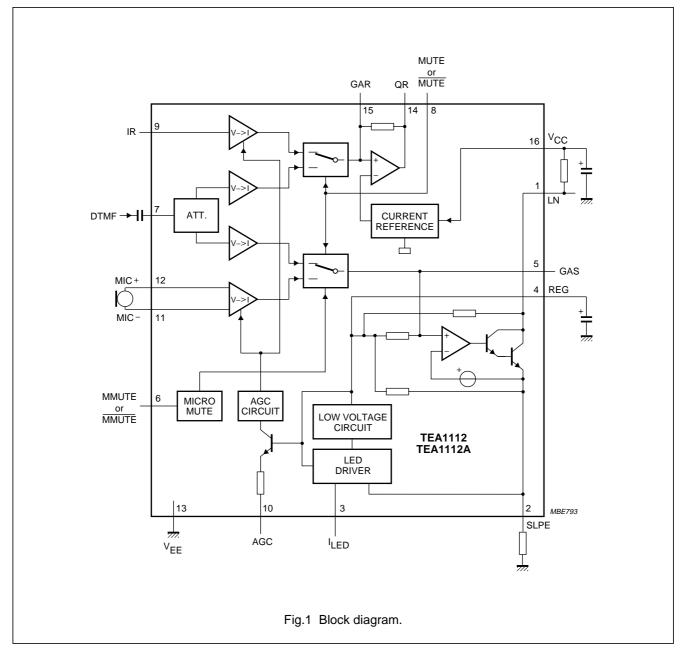
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>line</sub>	line current operating range	normal operation	11	-	140	mA
		with reduced performance	1	-	11	mA
I <sub>LED(max)</sub>	maximum supply current available	I <sub>line</sub> = 18 mA	-	0.5	-	mA
		I <sub>line</sub> > 76 mA	_	19.5	_	mA
V <sub>LN</sub>	DC line voltage		3.35	3.65	3.95	V
I <sub>CC</sub>	internal current consumption	V <sub>CC</sub> = 2.9 V	-	1.15	1.4	mA
V <sub>CC</sub>	supply voltage for peripherals	$I_p = 0 \text{ mA}$	_	2.9	_	V
G <sub>vtrx</sub>	typical voltage gain range					
	microphone amplifier	$V_{MIC} = 2 \text{ mV} (RMS)$	38.8	-	51.8	dB
	receiving amplifier	V <sub>IR</sub> = 6 mV (RMS)	19.2	-	31.2	dB
$\Delta G_{vtrx}$	gain control range for microphone and receiving amplifiers with respect to $I_{line} = 15 \text{ mA}$	I <sub>line</sub> = 85 mA	-	5.8	-	dB
$\Delta G_{vtxm}$	microphone amplifier gain reduction		_	80	_	dB

### TEA1112; TEA1112A

### **ORDERING INFORMATION**

TYPE		PACKAGE	
NUMBER	NAME	DESCRIPTION	VERSION
TEA1112	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
TEA1112A	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
TEA1112T	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
TEA1112AT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

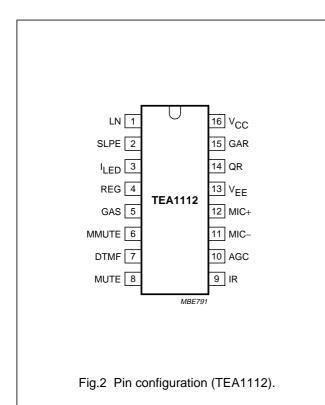
### **BLOCK DIAGRAM**

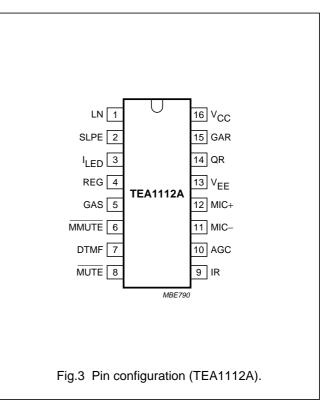


### TEA1112; TEA1112A

### PINNING

	P	PIN	DECODIDEICN				
SYMBOL	TEA1112	TEA1112A	DESCRIPTION				
LN	1	1	positive line terminal				
SLPE	2	2	slope (DC resistance) adjustment				
I <sub>LED</sub>	3	3	available output current to drive a LED				
REG	4	4	line voltage regulator decoupling				
GAS	5	5	sending gain adjustment				
MMUTE	6	_	microphone mute input				
MMUTE	-	6	microphone mute input (active LOW)				
DTMF	7	7	dual-tone multi-frequency input				
MUTE	8	_	mute input to select speech or dialling mode				
MUTE	-	8	mute input to select speech or dialling mode (active LOW)				
IR	9	9	receiving amplifier input				
AGC	10	10	automatic gain control/line loss compensation				
MIC-	11	11	inverting microphone amplifier input				
MIC+	12	12	non-inverting microphone amplifier input				
V <sub>EE</sub>	13	13	negative line terminal				
QR	14	14	receiving amplifier output				
GAR	15	15	receive gain adjustment				
V <sub>CC</sub>	16	16	supply voltage for speech circuit and peripherals				





TEA1112; TEA1112A

## Low voltage versatile telephone transmission circuits with dialler interface

### FUNCTIONAL DESCRIPTION

All data given in this chapter are typical values, except when otherwise specified.

### Supply (pins LN, SLPE, V<sub>CC</sub> and REG)

The supply for the TEA1112; TEA1112A and their peripherals is obtained from the telephone line.

The ICs generate a stabilized reference voltage (V<sub>ref</sub>) between pins LN and SLPE. This reference voltage is equal to 3.35 V, is temperature compensated and can be adjusted by means of an external resistor (R<sub>VA</sub>). It can be increased by connecting the RVA resistor between pins REG and SLPE (see Fig.5), or decreased by connecting the R<sub>VA</sub> resistor between pins REG and LN. The voltage at pin REG is used by the internal regulator to generate the stabilized reference voltage and is decoupled by a capacitor (C<sub>REG</sub>) which is connected to V<sub>EE</sub>. This capacitor, converted into an equivalent inductance (see Section "Set impedance"), realizes the set impedance conversion from its DC value (R<sub>SLPE</sub>) to its AC value (R<sub>CC</sub> in the audio-frequency range). The voltage at pin SLPE is proportional to the line current. Figure 4 illustrates the supply configuration.

The ICs regulate the line voltage at pin LN, and can be calculated as follows:

$$V_{LN} = V_{ref} + R_{SLPE} \times I_{SLPE}$$
$$I_{SLPE} = I_{line} - I_{CC} - I_{p} - I^{*} = I_{LED} + I_{sh}$$

#### Where:

I<sub>line</sub> = line current

 $I_{CC}$  = current consumption of the IC

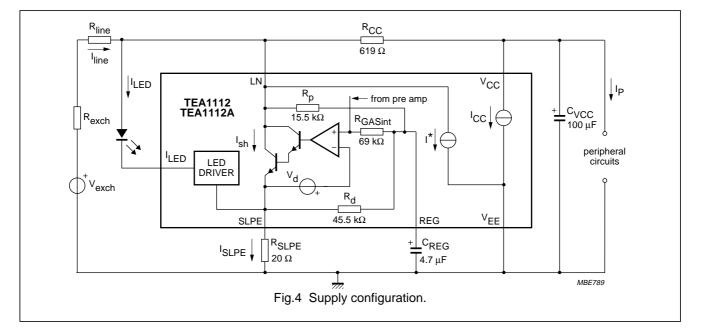
- $I_p$  = supply current for peripheral circuits
- $I^{\star}$  = current consumed between LN and  $V_{\text{EE}}$
- $I_{LED}$  = supply current for the LED component

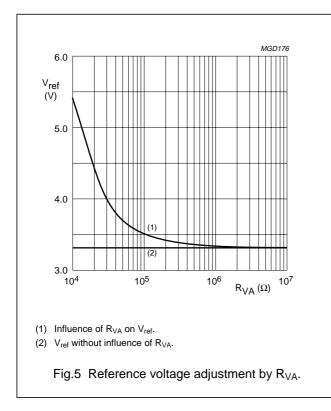
 $I_{sh}$  = the excess line current shunted to SLPE (and  $V_{EE})$  via LN.

The preferred value for  $R_{SLPE}$  is 20  $\Omega$ . Changing  $R_{SLPE}$  will affect more than the DC characteristics; it also influences the microphone and DTMF gains, the LED supply current characteristic, the gain control characteristics, the sidetone level and the maximum output swing on the line.

The internal circuitry of the TEA1112; TEA1112A is supplied from pin V<sub>CC</sub>. This voltage supply is derived from the line voltage by means of a resistor (R<sub>CC</sub>) and must be decoupled by a capacitor C<sub>VCC</sub>. It may also be used to supply peripheral circuits such as dialling or control circuits. The V<sub>CC</sub> voltage depends on the current consumed by the IC and the peripheral circuits as shown by the formula (see also Figs.6 and 7). R<sub>CCint</sub> is the internal impedance of the voltage supply point, and I<sub>rec</sub> is the current consumed by the output stage of the earpiece amplifier.

$$V_{CC} = V_{CC0} - R_{CCint} \times (I_p - I_{rec})$$
$$V_{CC0} = V_{LN} - R_{CC} \times I_{CC}$$





The DC line current flowing into the set is determined by the exchange supply voltage (V<sub>exch</sub>), the feeding bridge resistance (R<sub>exch</sub>), the DC resistance of the telephone line (R<sub>line</sub>) and the reference voltage (V<sub>ref</sub>). With line currents below 7.5 mA, the internal reference voltage (generating V<sub>ref</sub>) is automatically adjusted to a lower value. This means that more sets can operate in parallel with DC line voltages (excluding the polarity guard) down to an absolute minimum voltage of 1.6 V. At currents below 7.5 mA, the circuit has limited sending and receiving levels. This is called the low voltage area.

#### Set impedance

In the audio frequency range, the dynamic impedance is mainly determined by the  $R_{CC}$  resistor. The equivalent impedance of the circuits is illustrated in Fig.8.

### LED supply (pin I<sub>LED</sub>)

The TEA1112; TEA1112A give an on-hook/off-hook status indication. This is achieved by a current made available to drive an LED connected between pins  $I_{LED}$  and LN. In the low voltage area, which corresponds to low line current conditions, no current is available for this LED.

### TEA1112; TEA1112A

For line currents higher than a threshold,  $I_{LEDstart}$ , the  $I_{LED}$  current increases proportionally to the line current (with a ratio of one third). The  $I_{LED}$  current is internally limited to 19.5 mA (see Fig.9). If no LED device is used in the application, the  $I_{LED}$  pin should be shorted to pin SLPE.

For 17 mA < 
$$I_{line}$$
 < 77 mA:  $I_{LED} = \frac{I_{line} - 17}{3}$ 

This LED driver is referenced to SLPE. Consequently, all the  $I_{LED}$  supply current will flow through the  $R_{SLPE}$  resistor. The AGC characteristics are not disturbed (see Fig.4).

#### Microphone amplifier (pins MIC+, MIC- and GAS)

The TEA1112; TEA1112A have symmetrical microphone inputs. The input impedance between pins MIC+ and MIC- is 64 k $\Omega$  (2 × 32 k $\Omega$ ). The voltage gain from pins MIC+/MIC- to pin LN is set at 51.8 dB (typ). The gain can be decreased by connecting an external resistor R<sub>GAS</sub> between pins GAS and REG. The adjustment range is 13 dB. A capacitor C<sub>GAS</sub> connected between pins GAS and REG can be used to provide a first-order low-pass filter. The cut-off frequency corresponds to the time constant C<sub>GAS</sub> × (R<sub>GASint</sub> // R<sub>GAS</sub>). R<sub>GASint</sub> is the internal resistor which sets the gain with a typical value of 69 k $\Omega$ .

Automatic gain control is provided on this amplifier for line loss compensation.

#### Microphone mute (pin MMUTE; TEA1112)

The microphone amplifier can be disabled by activating the microphone mute function. When MMUTE is LOW, the normal speech mode is entered, depending on the level on MUTE (see Table 1). When MMUTE is HIGH, the microphone amplifier inputs are disabled while the DTMF input is enabled (no confidence tone is provided). The voltage gain between LN and MIC+/MIC- is attenuated; the gain reduction is 80 dB (typ).

#### Microphone mute (pin MMUTE; TEA1112A)

The microphone amplifier can be disabled by activating the microphone mute function. When MMUTE is LOW, the microphone amplifier inputs are disabled while the DTMF input is enabled (no confidence tone is provided). The voltage gain between LN and MIC+/MIC- is attenuated; the gain reduction is 80 dB (typ). When MMUTE is HIGH, the normal speech mode is entered, depending on the level on MUTE (see Table 1).

### Receiving amplifier (pins IR, GAR and QR)

The receiving amplifier has one input (IR) and one output (QR). The input impedance between pin IR and pin V<sub>EE</sub> is 20 kΩ. The voltage gain from pin IR to pin QR is set at 31.2 dB (typ). The gain can be decreased by connecting an external resistor R<sub>GAR</sub> between pins GAR and QR; the adjustment range is 12 dB. Two external capacitors C<sub>GAR</sub> (connected between GAR and QR) and C<sub>GARS</sub> (connected between GAR and V<sub>EE</sub>) ensure stability. The C<sub>GAR</sub> capacitor provides a first-order low-pass filter. The cut-off frequency corresponds to the time constant C<sub>GAR</sub> × (R<sub>GARint</sub> // R<sub>GAR</sub>). R<sub>GARint</sub> is the internal resistor which sets the gain with a typical value of 100 kΩ. The relationship C<sub>GARS</sub> = 10 × C<sub>GAR</sub> must be fulfilled to ensure stability.

The output voltage of the receiving amplifier is specified for continuous wave drive. The maximum output swing depends on the DC line voltage, the  $R_{CC}$  resistor, the  $I_{CC}$  current consumption of the circuit, the  $I_p$  current consumption of the peripheral circuits and the load impedance.

Automatic gain control is provided on this amplifier for line loss compensation.

### Automatic gain control (pin AGC)

The TEA1112; TEA1112A perform automatic line loss compensation. The automatic gain control varies the gain of the microphone amplifier and the gain of the receiving amplifier in accordance with the DC line current. The control range is 5.8 dB (which corresponds approximately to a line length of 5 km for a 0.5 mm diameter twisted-pair copper cable with a DC resistance of 176  $\Omega$ /km and an average attenuation of 1.2 dB/km). The ICs can be used with different configurations of feeding bridge (supply voltage and bridge resistance) by connecting an external resistor R<sub>AGC</sub> between pins AGC and V<sub>EE</sub>. This resistor enables the I<sub>start</sub> and I<sub>stop</sub> line currents to be increased (the ratio between I<sub>start</sub> and I<sub>stop</sub> is not affected by the resistor). The AGC function is disabled when pin AGC is left open-circuit.

### Mute function (pin MUTE; TEA1112)

The mute function performs the switching action between the speech mode and the dialling mode. When MUTE is LOW or open-circuit, the microphone and receiving amplifiers inputs are enabled while the DTMF input is disabled, depending on the MMUTE level (see Table 1). When MUTE is HIGH, the DTMF input is enabled and the microphone and receiving amplifiers inputs are disabled.

### Mute function (pin MUTE; TEA1112A)

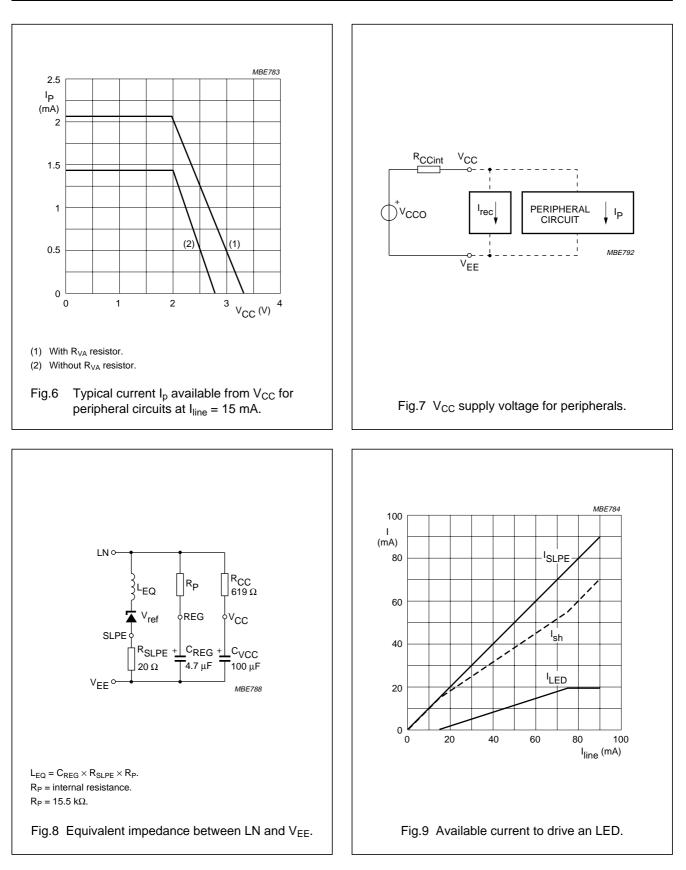
The mute function performs the switching between the speech mode and the dialling mode. When MUTE is LOW or open-circuit, the DTMF input is enabled and the microphone and receiving amplifiers inputs are disabled. When MUTE is HIGH, the microphone and receiving amplifiers inputs are enabled while the DTMF input is disabled, depending on the MMUTE level (see Table 1).

### DTMF amplifier (pin DTMF)

When the DTMF amplifier is enabled, dialling tones may be sent on line. These tones can be heard in the earpiece at a low level (confidence tone).

The TEA1112; TEA1112A have an asymmetrical DTMF input. The input impedance between DTMF and  $V_{EE}$  is 20 k $\Omega$ . The voltage gain from pin DTMF to pin LN is 25.5 dB. When an external resistor is connected between pins REG and GAS to decrease the microphone gain, the DTMF gain varies in the same way (the DTMF gain is 26.3 dB lower than the microphone gain with no AGC control).

The automatic gain control has no effect on the DTMF amplifier.



### TEA1112; TEA1112A

#### MUTE and MMUTE levels for different modes

Table 1 Required MUTE and MMUTE levels to enable the different possible modes

IC	TEA	1112	TEA1	1112A			
Mode	MUTE	MMUTE	MUTE	MMUTE			
Speech	L	L	Н	Н			
DTMF dialling	Н	Х	L	Х			
Microphone mute	L H		Н	L			

#### SIDETONE SUPPRESSION

The TEA1112; TEA1112A anti-sidetone network comprising R<sub>CC</sub> // Z<sub>line</sub>, R<sub>ast1</sub>, R<sub>ast2</sub>, R<sub>ast3</sub>, R<sub>SLPE</sub> and Z<sub>bal</sub> (see Fig.10) suppresses the transmitted signal in the earpiece. Maximum compensation is obtained when the following conditions are fulfilled:

$$R_{SLPE} \times R_{ast1} = R_{CC} \times (R_{ast2} + R_{ast3})$$

$$k = \frac{(R_{ast2} \times (R_{ast3} + R_{SLPE}))}{(R_{ast1} \times R_{SLPE})}$$

 $Z_{bal} = k \times Z_{line}$ 

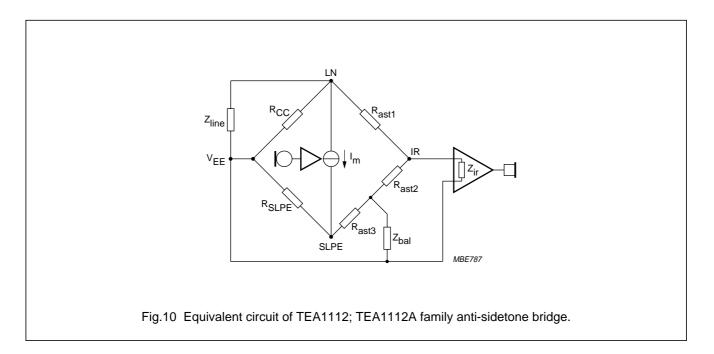
The scale factor k is chosen to meet the compatibility with a standard capacitor from the E6 or E12 range for  $Z_{bal}$ .

In practice,  $Z_{line}$  varies considerably with the line type and the line length. Therefore, the value chosen for  $Z_{bal}$  should

be for an average line length which gives satisfactory sidetone suppression with short and long lines. The suppression also depends on the accuracy of the match between  $Z_{\text{bal}}$  and the impedance of the average line.

The anti-sidetone network for the TEA1112; TEA1112A (as shown in Fig.14) attenuates the receiving signal from the line by 32 dB before it enters the receiving amplifier. The attenuation is almost constant over the whole audio frequency range. A Wheatstone bridge configuration (see Fig.11) may also be used.

More information on the balancing of an anti-sidetone bridge can be obtained in our publication *"Applications Handbook for Wired Telecom Systems, IC03b"*, order number 9397 750 00811.



### TEA1112; TEA1112A

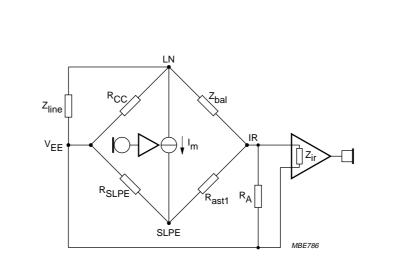


Fig.11 Equivalent circuit of an anti-sidetone network in a Wheatstone bridge configuration.

### LIMITING VALUES

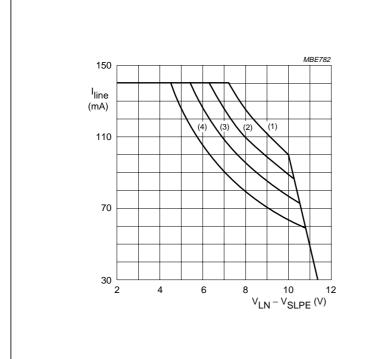
In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>LN</sub>	positive continuous line voltage		$V_{EE} - 0.4$	12	V
	repetitive line voltage during switch-on or line interruption		V <sub>EE</sub> – 0.4	13.2	V
V <sub>n(max)</sub>	maximum voltage on pins ILED, SLPE		$V_{EE} - 0.4$	V <sub>LN</sub> + 0.4	V
	maximum voltage on all other pins		$V_{EE} - 0.4$	V <sub>CC</sub> + 0.4	V
I <sub>line</sub>	line current	$R_{SLPE} = 20 \Omega$ ; see Figs 12 and 13	-	140	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 75 °C;			
	TEA1112; TEA1112A	see Figs 12 and 13	-	625	mW
	TEA1112T; TEA1112AT		-	416	mW
T <sub>stg</sub>	IC storage temperature		-40	+125	°C
T <sub>amb</sub>	operating ambient temperature		-25	+75	°C

### THERMAL CHARACTERISTICS

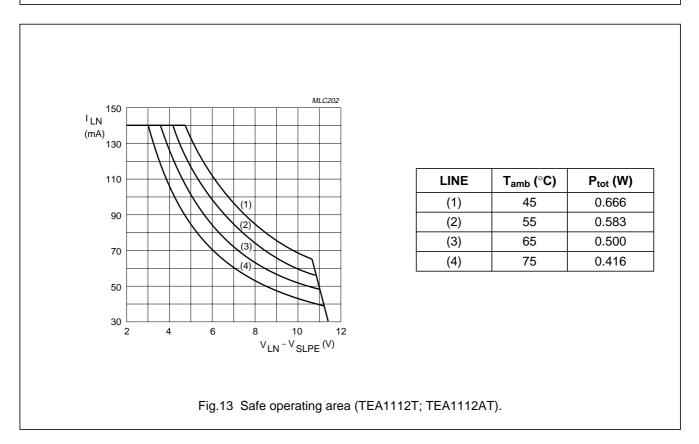
SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient in free air (TEA1112; TEA1112A)	80	K/W
	thermal resistance from junction to ambient in free air mounted on epoxy board 40.1 $\times$ 19.1 $\times$ 1.5 mm (TEA1112T; TEA1112AT)	130	K/W

### TEA1112; TEA1112A



LINE	T <sub>amb</sub> (°C)	P <sub>tot</sub> (W)
(1)	45	1.000
(2)	55	0.875
(3)	65	0.750
(4)	75	0.625

### Fig.12 Safe operating area (TEA1112; TEA1112A).



### TEA1112; TEA1112A

### CHARACTERISTICS

 $I_{line}$  = 15 mA;  $V_{EE}$  = 0 V;  $R_{SLPE}$  = 20  $\Omega$ ; AGC pin connected to  $V_{EE}$ ;  $Z_{line}$  = 600  $\Omega$ ; f = 1 kHz;  $T_{amb}$  = 25 °C; unless otherwise specified.

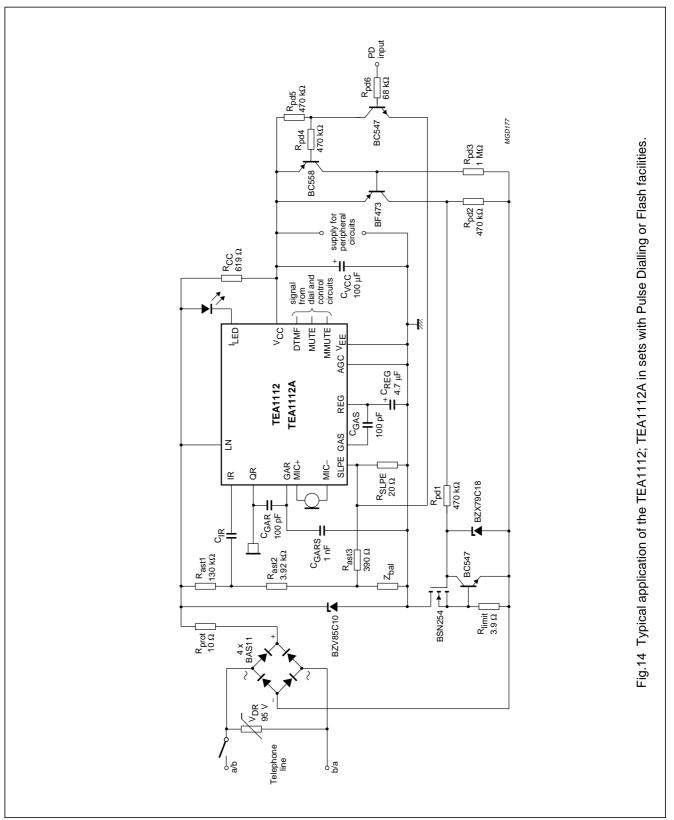
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supply (pi	ins V <sub>LN</sub> , V <sub>CC</sub> , SLPE and REG)		•		ł	
V <sub>ref</sub>	stabilized voltage between LN and SLPE		3.1	3.35	3.6	V
V <sub>LN</sub>	DC line voltage	I <sub>line</sub> = 1 mA	-	1.6	-	V
		I <sub>line</sub> = 4 mA	-	2.45	-	V
		I <sub>line</sub> = 15 mA	3.35	3.65	3.95	V
		I <sub>line</sub> = 140 mA	-	-	6.9	V
V <sub>LN(exR)</sub>	DC line voltage with an external resistor $R_{\text{VA}}$	$R_{VA(SLPE-REG)} = 27 \ k\Omega$	-	4.4	-	V
$\Delta V_{LN(T)}$	DC line voltage variation with temperature referred to 25 °C	$T_{amb} = -25$ to +75 °C	-	±30	-	mV
I <sub>CC</sub>	internal current consumption	V <sub>CC</sub> = 2.9 V	-	1.15	1.4	mA
V <sub>CC</sub>	supply voltage for peripherals	$I_p = 0 \text{ mA}$	-	2.9	-	V
R <sub>CCint</sub>	equivalent supply voltage impedance	I <sub>p</sub> = 0.5 mA	_	550	620	Ω
LED supp	ly (pin I <sub>LED</sub> )					
I <sub>line(h)</sub>	highest line current for $I_{LED} < 0.5$ mA		_	18	-	mA
I <sub>line(I)</sub>	lowest line current for maximum ILED		-	76	-	mA
I <sub>LED(max)</sub>	maximum supply current available		-	19.5	-	mA
Micropho	ne amplifier (pins MIC+, MIC– and G	AS)		ł		
Z <sub>i</sub>	input impedance					
	differential between pins MIC+ and MIC-		-	64	-	kΩ
	single-ended between pins MIC+/MIC- and V <sub>EE</sub>		-	32	-	kΩ
G <sub>vtx</sub>	voltage gain from MIC+/MIC- to LN	V <sub>MIC</sub> = 2 mV (RMS)	50.6	51.8	53	dB
$\Delta G_{vtx(f)}$	gain variation with frequency referred to 1 kHz	f = 300 to 3400 Hz	-	±0.2	-	dB
$\Delta G_{\text{vtx}(\text{T})}$	gain variation with temperature referred to 25 °C	$T_{amb} = -25$ to +75 °C	-	±0.3	-	dB
CMRR	common mode rejection ratio		-	80	-	dB
$\Delta G_{vtxr}$	gain voltage reduction range	external resistor connected between GAS and REG	-	-	13	dB
V <sub>LN(max)</sub>	maximum sending signal	I <sub>line</sub> = 15 mA; THD = 2%	1.4	1.7	-	V
-	(RMS value)	I <sub>line</sub> = 4 mA; THD = 10%	-	0.8	-	V
V <sub>notx</sub>	noise output voltage at pin LN; pins MIC+/ MIC– shorted through 200 $\Omega$	psophometrically weighted (P53 curve)	-	-70.5	-	dBmp

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Microphor	he mute (pins MMUTE; TEA1112 and	MMUTE; TEA1112A)				1
$\Delta G_{\text{vtxm}}$	gain reduction in microphone MUTE mode		-	80	-	dB
VIL	LOW level input voltage		$V_{\text{EE}} - 0.4$	-	V <sub>EE</sub> + 0.3	V
V <sub>IH</sub>	HIGH level input voltage		V <sub>EE</sub> + 1.5	-	V <sub>CC</sub> + 0.4	V
I <sub>MMUTE</sub>	input current	input level = HIGH	_	1.25	3	μA
Receiving	amplifier (pins IR, QR and GAR)					-
Z <sub>i</sub>	input impedance		-	20	-	kΩ
G <sub>vrx</sub>	voltage gain from IR to QR	V <sub>IR</sub> = 6 mV (RMS)	29.7	31.2	32.7	dB
$\Delta G_{vrx(f)}$	gain variation with frequency referred to 1 kHz	n variation with frequency f = 300 to 3400 Hz –		±0.2	-	dB
$\Delta G_{vrx(T)}$	gain variation with temperature referred to 25 °C			±0.3	-	dB
$\Delta G_{vrxr}$	gain voltage reduction range	external resistor connected between GAR and QR	-	-	12	dB
V <sub>o(rms)</sub>	maximum receiving signal (RMS value)	$I_p = 0$ mA sine wave drive; R <sub>L</sub> = 150 Ω; THD = 2%	-	0.25	-	V
		$I_p = 0$ mA sine wave drive; R <sub>L</sub> = 450 $\Omega$ ; THD = 2%	-	0.35	_	V
V <sub>norx(rms)</sub>	noise output voltage at pin QR (RMS value)	IR open-circuit; $R_L = 150 \Omega$ ; psophometrically weighted (P53 curve)	-	-86	-	dBVp
Automatic	gain control (pin AGC)					
$\Delta G_{vtrx}$	gain control range for microphone and receiving amplifiers with respect to $I_{line} = 15 \text{ mA}$	I <sub>line</sub> = 85 mA	-	5.8	-	dB
I <sub>start</sub>	highest line current for maximum gain		-	26	-	mA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>stop</sub>	lowest line current for minimum gain		-	61	-	mA
DTMF amp	olifier (pin DTMF)					
Z <sub>i</sub>	input impedance		-	20	-	kΩ
G <sub>vdtmf</sub>	voltage gain from DTMF to LN in DTMF dialling or microphone MUTE mode	voltage gain from DTMF to LN in DTMF dialling or microphone MUTE		25.5	26.7	dB
$\Delta G_{vdtmf(f)}$	gain variation with frequency f = 300 to 3400 Hz - referred to 1 kHz		-	±0.2	_	dB
$\Delta G_{vdtmf(T)}$	gain variation with temperature referred to 25 °C	$T_{amb} = -25 \text{ to } +75 ^\circ\text{C}$	-	±0.4	-	dB
G <sub>vct</sub>	voltage gain from DTMF to QR (confidence tone)	$V_{DTMF}$ = 20 mV (RMS); R <sub>L</sub> = 150 $\Omega$	-	-18	-	dB
Mute func	tion (pins MUTE; TEA1112 and MUT	Ē; TEA1112A)	•			
V <sub>IL</sub>	LOW level input voltage		V <sub>EE</sub> - 0.4	_	V <sub>EE</sub> + 0.3	V
V <sub>IH</sub>	HIGH level input voltage		V <sub>EE</sub> + 1.5	_	V <sub>CC</sub> + 0.4	V
I <sub>MUTE</sub>	input current	input level = HIGH	-	1.25	3	μA
$\Delta G_{trxm}$	gain reduction for microphone and receiving amplifiers in DTMF dialling mode		-	80	-	dB

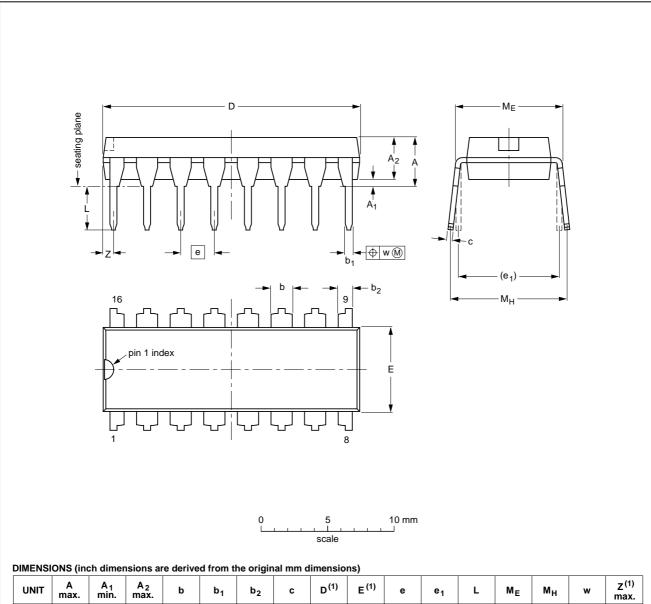
## TEA1112; TEA1112A

### **APPLICATION INFORMATION**



### PACKAGE OUTLINES

### DIP16: plastic dual in-line package; 16 leads (300 mil)

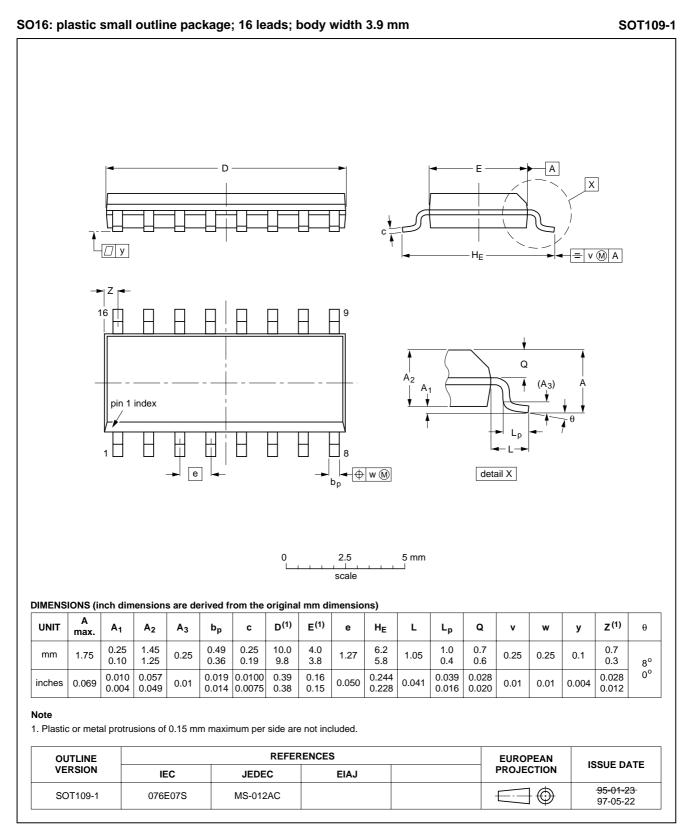


UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	b <sub>2</sub>	с	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	L	ME	м <sub>н</sub>	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.030

#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLIN	NE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSIC	ON	IEC	JEDEC	EIAJ	PROJECTION	1550E DATE	
SOT38	-4					<del>-92-11-17-</del> 95-01-14	



### TEA1112; TEA1112A

### SOLDERING

### Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

### DIP

#### SOLDERING BY DIPPING OR BY WAVE

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ( $T_{stg\,max}$ ). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

#### REPAIRING SOLDERED JOINTS

Apply a low voltage soldering iron (less than 24 V) to the lead(s) of the package, below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

### SO

#### **REFLOW SOLDERING**

Reflow soldering techniques are suitable for all SO packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45  $^{\circ}$ C.

#### WAVE SOLDERING

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### REPAIRING SOLDERED JOINTS

Fix the component by first soldering two diagonallyopposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

### TEA1112; TEA1112A

### DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
more of the limiting values of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification limiting values for extended periods may affect device reliability.
Application information	

Where application information is given, it is advisory and does not form part of the specification.

### LIFE SUPPORT APPLICATIONS

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